

Transistors

# 2.5V Drive Nch MOSFET

## RTF025N03

●Structure

Silicon N-channel MOSFET

●Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (2.5V drive).

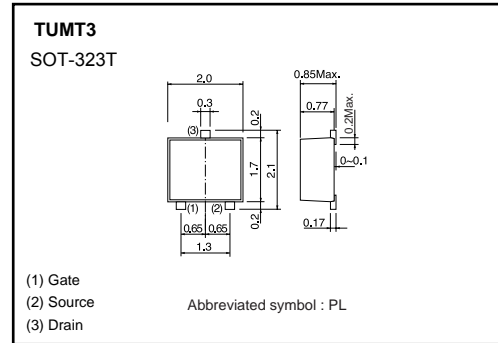
●Applications

Switching

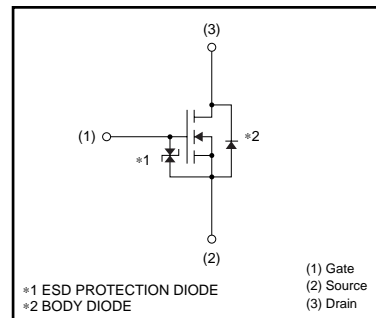
●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RTF025N03		○

●Dimensions (Unit : mm)



●Inner circuit

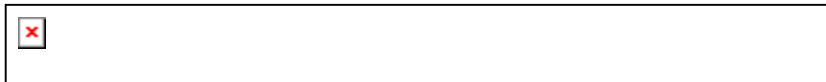


●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	30	V	
Gate-source voltage	$V_{GSS}$	12	V	
Drain current	Continuous	$I_D$	±2.5	A
	Pulsed	$I_{DP}$ *1	±10	A
Source current (Body diode)	Continuous	$I_S$	0.6	A
	Pulsed	$I_{SP}$ *1	10	A
Total power dissipation	$P_D$ *2	0.8	W	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

\*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$   
\*2 Mounted on a ceramic board

●Thermal resistance



## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	10	$\mu A$	$V_{GS}=12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	1	$\mu A$	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.5	–	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	48	67	$m\Omega$	$I_D=2.5A, V_{GS}=4.5V$
		–	50	70	$m\Omega$	$I_D=2.5A, V_{GS}=4V$
		–	70	98	$m\Omega$	$I_D=2.5A, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	2	–	–	S	$V_{DS}=10V, I_D=2.5A$
Input capacitance	$C_{iss}$	–	270	–	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	–	70	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	–	40	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	8	–	ns	$V_{DD}\doteq 15V$
Rise time	$t_r$ *	–	15	–	ns	$I_D=1.25A$
Turn-off delay time	$t_{d(off)}$ *	–	27	–	ns	$V_{GS}=4.5V$
Fall time	$t_f$ *	–	11	–	ns	$R_L=12\Omega$
Total gate charge	$Q_g$ *	–	3.7	5.2	nC	$V_{DD}\doteq 15V$
Gate-source charge	$Q_{gs}$ *	–	0.7	–	nC	$V_{GS}=4.5V$
Gate-drain charge	$Q_{gd}$ *	–	1.2	–	nC	$I_D=2.5A$

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}$	–	–	1.2	V	$I_S=0.6A, V_{GS}=0V$

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